Wolfspeed’s G50V4 is a high performance 50 V microwave process targeting applications operating at frequencies from DC through 14 GHz. The process has been fully qualified with the qualification report available upon request. The drain voltage of 50 V with breakdown of 150 V optimizes this process for high performance applications where high power and efficiency over wide bandwidths is required.

The process features two gold RF interconnect layers, MMIC capacitors, thin film and bulk GaN resistors, and dielectrically supported bridges for connections to circuit elements such as capacitors and inductors. The Silicon Carbide substrate thickness is 100 microns and has the smallest substrate VIA sizes available in a GaN on SiC MMIC process, which enables very compact FET footprint for high frequency applications. Process Design Kits (PDKs) with scalable, accurate models of the G50V4 devices are available for Microwave Office (MWO) or Advanced Design System (ADS) simulators. The PDKs have been vetted for both small signal and large signal accuracy. Model validation reports are available upon request.

**FEATURES**

- 0.25μm Gate Length
- \( V_p \sim -2.7\) V
- 50 V Bias with >150 V Breakdown
- Performance DC-14 GHz
- >15 dB Gain @ 10 GHz
- \( P_{sat} = 8.5\) W/mm @ 10 GHz
- Peak PAE = 55% @ 10 GHz
- Metal1 = 3μm; Metal2 = 3μm
- MIM Cap 180pF/mm²
- TFR 12 Ω/sq
- GaN Resistors: 70 and 395 Ω/sq
- Protective Scratch Coat Top Layer
- Substrate Thickness: 100μm
- Substrate VIAs
- Au Back Metal

**CIRCUIT TYPES**

- High Power Amplifiers
- Low Noise Amplifiers
- RF Switches
- Phase-Shifters
- Attenuators

**APPLICATIONS**

- RADAR
- Telecom
- Point-to-Point Radio
- Ultra-wide Band EW
- ECM

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ASK ABOUT THE GaN RF FOUNDRY ONLINE TRAINING COURSE.
G50V4 GaN ON SIC 0.25\(\mu\)M MMIC FOUNDRY PROCESS

FOUNDRY SERVICES

Customers can design and fabricate circuits through Wolfspeed’s foundry using development or production lots. Designs from development masks are easily ported to production mask sets for volume production. Wolfspeed foundry is a high volume manufacturer and can handle all your production needs.

![Graph showing Maximum Available Gain vs Frequency for G50V4 GaN on SIC 0.25\(\mu\)M MMIC Foundry Process]

![Graph showing Load Pull Power Tune for G50V4 GaN on SIC 0.25\(\mu\)M MMIC Foundry Process]

DESIGN TOOLS

- Design Manual
- Device Library of Circuit Elements: FETs, Thin Film Resistors, Bulk Resistors, Capacitors, Inductors
- Design Kit for ADS Design Environment
- Design Kit for AWR Microwave Office
- Design Rule Check
- Tiling of GDSII Stream Files
- On-wafer Test Development
- Failure Analysis
- Mask Procurement
- Production 100mm Wafer
- Wafer Thinning
- Wafer Singulation
- Substrate VIAs
- DC Test
- RF On-wafer Test
- Custom Design Services
- Die Pick
- Wafer Delivery on Tape

SUPPORT FEATURES

- Process Design Kits
- Design Rule Check
- Tiling of GDSII Stream Files
- On-wafer Test Development
- Failure Analysis
- Mask Procurement
- Production 100mm Wafer
- Wafer Thinning
- Wafer Singulation
- Substrate VIAs
- DC Test
- RF On-wafer Test
- Custom Design Services
- Die Pick
- Wafer Delivery on Tape